

Supplementary Material (ESI)

Electronic Supplementary Information

Structures, Electric Properties and STM Images of GeSe Monolayers Doped by Group IV–VI Atoms: A First-Principles Study

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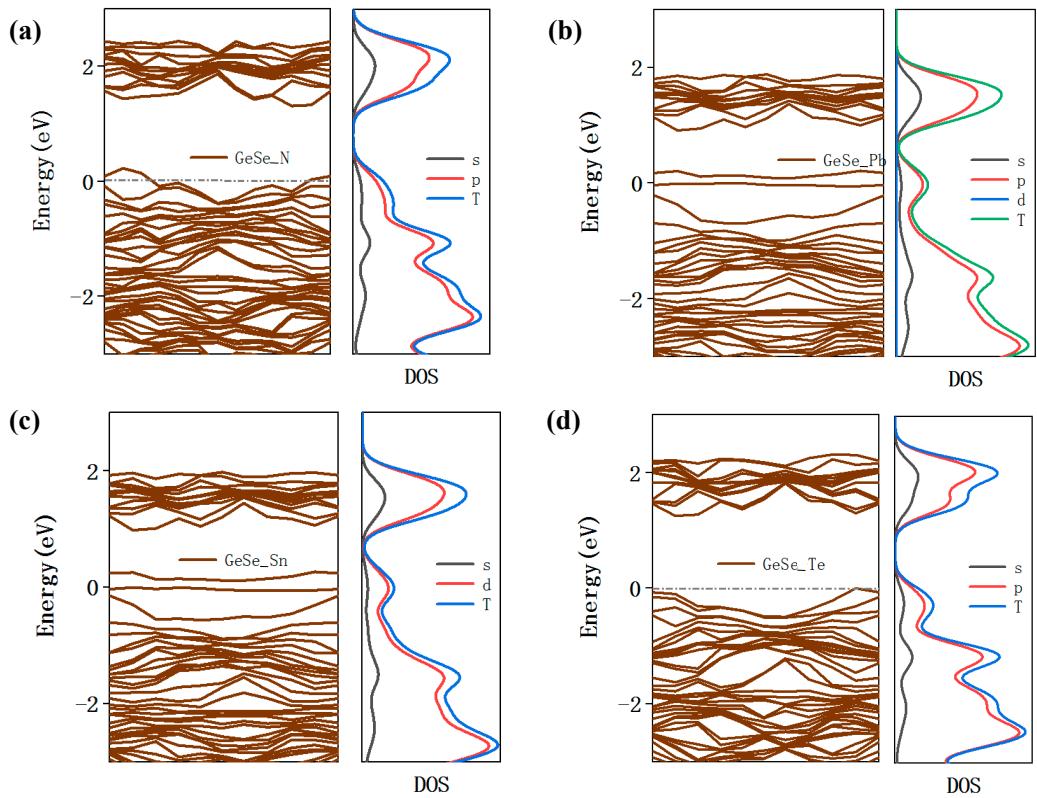


Figure S1. Bandgap structure and the corresponding DOS of GeSe_N, GeSe_Pb, GeSe_Sn and GeSe_Te.

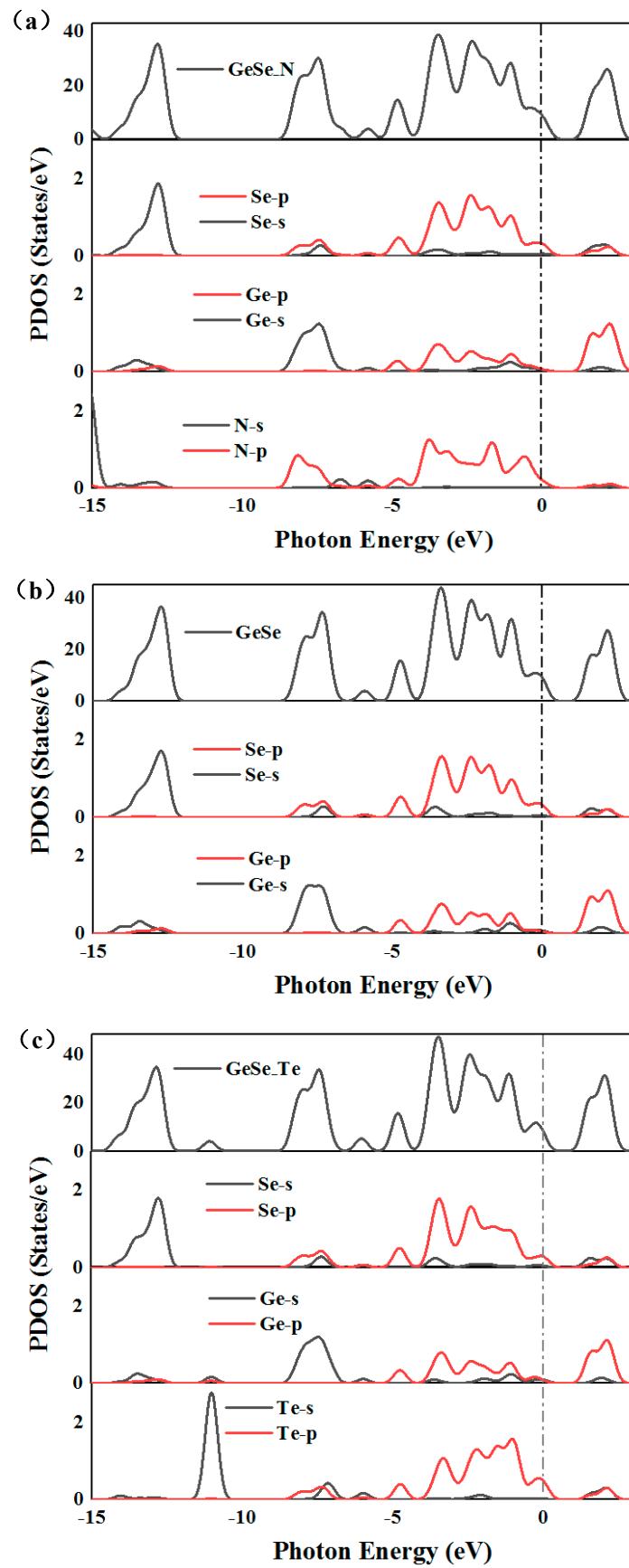


Figure S2. DOS and PDOS comparison of GeSe_N, pure GeSe and GeSe_Te.